

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A magnetic memory device comprising:

a memory cell which includes a first wiring line composed of a first wiring layer, a second wiring line composed of a second wiring layer and provided above or below the first wiring line so as to cross the first wiring line, and a magnetoresistive effect element device provided in a position where the first wiring line and the second wiring line cross each other; and

a peripheral circuit which includes a third wiring line provided around the memory cell and composed of the first wiring layer, a fourth wiring line provided above or below the third wiring line and composed of the second wiring layer, and a magnetic layer provided between the third wiring line and the fourth wiring line and separated from both of the third wiring line and the fourth wiring line, and the magnetic layer electrically connected to only one of the third wiring line and the fourth wiring line via a nonmagnetic layer, the magnetic layer insulated from either the third wiring line or the fourth wiring line by an insulator film, wherein the insulator film is an interlayer insulator film.

Claim 2 (Original): The magnetic memory device according to claim 1, wherein the magnetic layer is provided so as to correspond to at least a part of the third wiring line and the fourth wiring line.

Claim 3 (Original): The magnetic memory device according to claim 1, wherein the magnetoresistive effect element device has a three-layered structure including two magnetic layers and a nonmagnetic layer provided between the two magnetic layers.

Claim 4 (Original): The magnetic memory device according to claim 1, wherein the first and second wiring lines have each a yoke structure.

Claim 5 (Original): The magnetic memory device according to claim 1, wherein at least one of the first to fourth wiring lines has a yoke structure.

Claim 6 (Original): The magnetic memory device according to claim 1, wherein the memory cell further includes a switching element device electrically connected to the magnetoresistive effect element device.

Claim 7-13 (Cancelled).

Claim 14 (Previously Presented): The magnetic memory device according to claim 1, wherein the magnetic layer is composed of a magnetic layer used to form the magnetoresistive effect element device in the memory cell.

Claim 15 (New): The magnetic memory device according to claim 1, wherein an insulator film is provided between the other of the third wiring line and the fourth wiring line and the magnetic layer, and the insulator film is an interlayer insulator film.

Claim 16 (New): The magnetic memory device according to claim 1, wherein the magnetic layer is a single layer.

Claim 17 (New): The magnetic memory device according to claim 1, wherein the nonmagnetic layer is composed of a nonmagnetic layer used to form the magnetoresistive effect element device of the memory cell.